TN0110

N-Channel Enhancement-Mode Vertical DMOS FET

Features

- 2V Maximum Low Threshold
- High Input Impedance
- 50 pF Typical Low Input Capacitance
- Fast Switching Speeds
- Low On-Resistance
- Free from Secondary Breakdown
- Low Input and Output Leakage

Applications

- Logic-Level Interfaces (Ideal for TTL and CMOS)
- Solid-State Relays
- Battery-Operated Systems
- Photovoltaic Drives
- Analog Switches
- General Purpose Line Drivers
- Telecommunication Switches

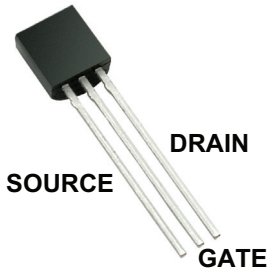
General Description

The TN0110 low-threshold Enhancement-mode (normally-off) transistor uses a vertical DMOS structure and a well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally induced secondary breakdown.

Microchip's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Package Type

3-lead TO-92
(Top view)



See Table 3-1 for pin information.

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings†

Drain-to-Source Voltage ..... BV_{DSS}
Drain-to-Gate Voltage ..... BV_{DGS}
Gate-to-Source Voltage ..... ±20V
Operating Ambient Temperature, T_A ..... –55°C to +150°C
Storage Temperature, T_S ..... –55°C to +150°C

† Notice: Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Electrical Specifications: T_A = 25°C unless otherwise specified. All DC parameters are 100% tested at 25°C unless otherwise stated. (Pulse test: 300 µs pulse, 2% duty cycle)

Parameter	Sym.	Min.	Typ.	Max.	Unit	Conditions
Drain-to-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	V_{GS} = 0V, I_D = 1 mA
Gate Threshold Voltage	$V_{GS(th)}$	0.6	—	2	V	V_{GS} = V_{DS}, I_D = 0.5 mA
Change in $V_{GS(th)}$ with Temperature	$\Delta V_{GS(th)}$	—	–3.2	–5	mV/°C	V_{GS} = V_{DS}, I_D = 1 mA (**Note 1**)
Gate Body Leakage Current	I_{GSS}	—	—	100	nA	V_{GS} = ± 20V, V_{DS} = 0V
Zero-Gate Voltage Drain Current	I_{DSS}	—	—	10	µA	V_{GS} = 0V, V_{DS} = Maximum rating
		—	—	500	µA	V_{DS} = 0.8 Maximum rating, V_{GS} = 0V, T_A = 125°C (**Note 1**)
On-State Drain Current	$I_{D(ON)}$	0.75	1.4	—	A	V_{GS} = 5V, V_{DS} = 25V
		2	3.4	—	A	V_{GS} = 10V, V_{DS} = 25V
Static Drain-to-Source On-State Resistance	$R_{DS(ON)}$	—	2	4.5	Ω	V_{GS} = 4.5V, I_D = 250 mA
		—	1.6	3	Ω	V_{GS} = 10V, I_D = 500 mA
Change in $R_{DS(ON)}$ with Temperature	$\Delta R_{DS(ON)}$	—	0.6	1.1	%/°C	V_{GS} = 10V, I_D = 500 mA (**Note 1**)

Note 1: Specification is obtained by characterization and is not 100% tested.

AC ELECTRICAL CHARACTERISTICS

Electrical Specifications: T_A = 25°C unless otherwise specified. Specification is obtained by characterization and is not 100% tested.						
Parameter	**Sym.**	**Min.**	**Typ.**	**Max.**	**Unit**	**Conditions**
Forward Transconductance	G_{FS}	225	400	—	mmho	V_{DS} = 25V, I_D = 500 mA
Input Capacitance	C_{ISS}	—	50	60	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1 MHz
Common-Source Output Capacitance	C_{OSS}	—	25	35	pF	
Reverse Transfer Capacitance	C_{RSS}	—	4	8	pF	
Turn-On Delay Time	$t_{d(ON)}$	—	2	5	ns	V_{DD} = 25V, I_D = 1A, R_{GEN} = 25Ω
Rise Time	t_r	—	3	5	ns	
Turn-Off Delay Time	$t_{d(OFF)}$	—	6	7	ns	
Fall Time	t_f	—	3	6	ns	
DIODE PARAMETER						
Diode Forward Voltage Drop	V_{SD}	—	1	1.5	V	V_{GS} = 0V, I_{SD} = 500 mA (**Note 1**)
Reverse Recovery Time	t_{rr}	—	400	—	ns	V_{GS} = 0V, I_{SD} = 500 mA

Note 1: All DC parameters are 100% tested at 25°C unless otherwise stated. (Pulse test: 300 µs pulse, 2% duty cycle)

TEMPERATURE SPECIFICATIONS

Parameter	**Sym.**	**Min.**	**Typ.**	**Max.**	**Unit**	**Conditions**
TEMPERATURE RANGE						
Operating Ambient Temperature	T_A	–55	—	+150	°C	
Storage Temperature	T_S	–55	—	+150	°C	
PACKAGE THERMAL RESISTANCE						
3-lead TO-92	θ_{JA}	—	132	—	°C/W	

THERMAL CHARACTERISTICS

Package	**I_D (Note 1) (Continuous) (mA)**	**I_D (Pulsed) (A)**	**Power Dissipation at T_A = 25°C (W)**	**I_{DR} (Note 1) (mA)**	**I_{DRM} (A)**
3-lead TO-92	350	2	1	350	2

Note 1: I_D (continuous) is limited by maximum rated T_J.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g. outside specified power supply range) and therefore outside the warranted range.

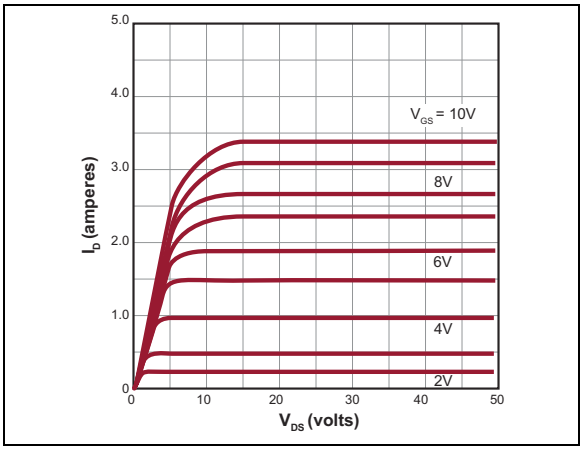


FIGURE 2-1: *Output Characteristics.*

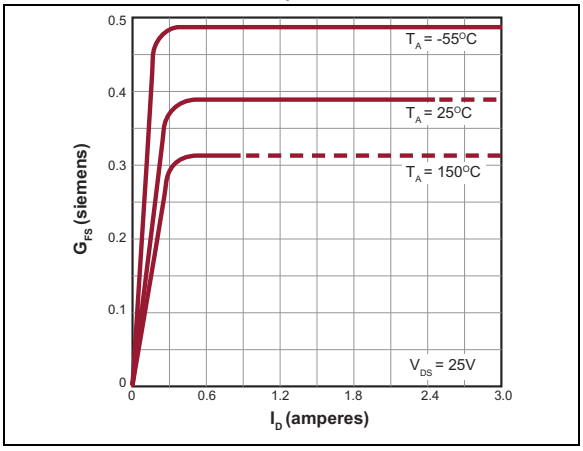


FIGURE 2-2: *Transconductance vs. Drain Current.*

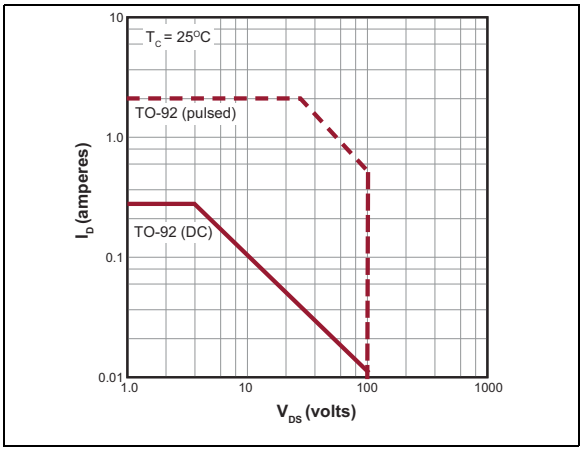


FIGURE 2-3: *Maximum Rated Safe Operating Area.*

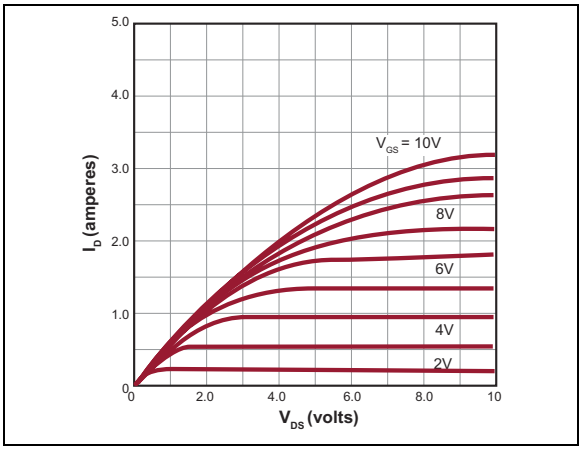


FIGURE 2-4: *Saturation Characteristics.*

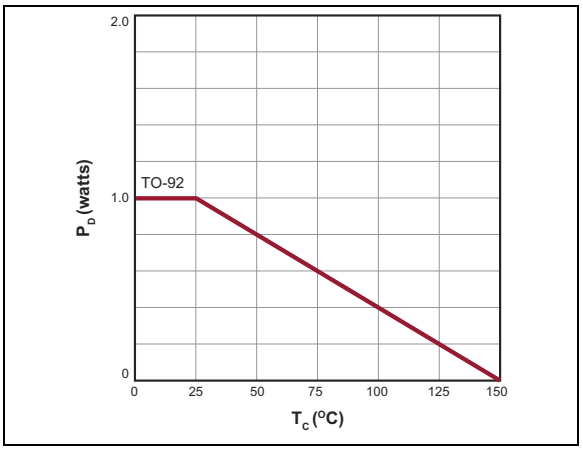


FIGURE 2-5: *Power Dissipation vs. Case Temperature.*

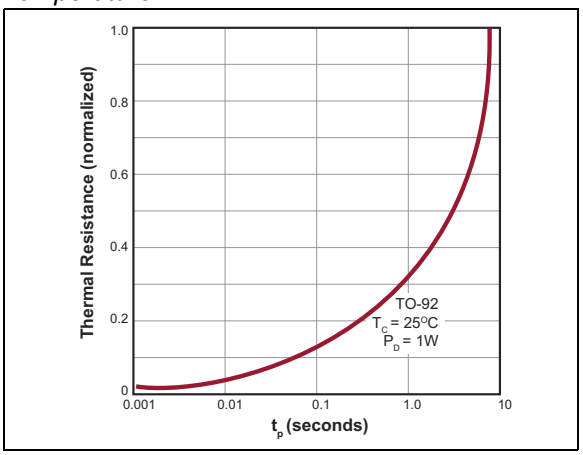


FIGURE 2-6: *Thermal Response Characteristics.*

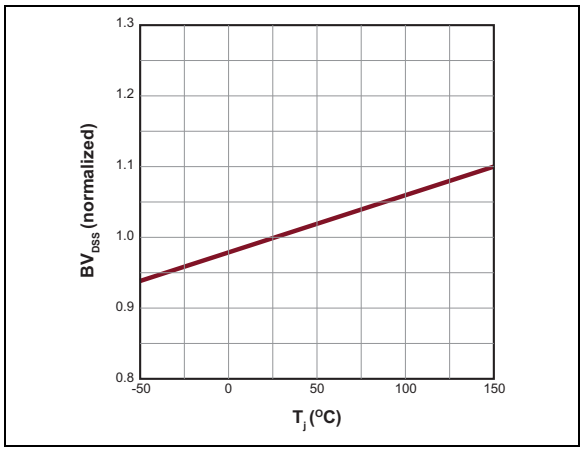


FIGURE 2-7: *BV_{DSS} Variation with Temperature.*

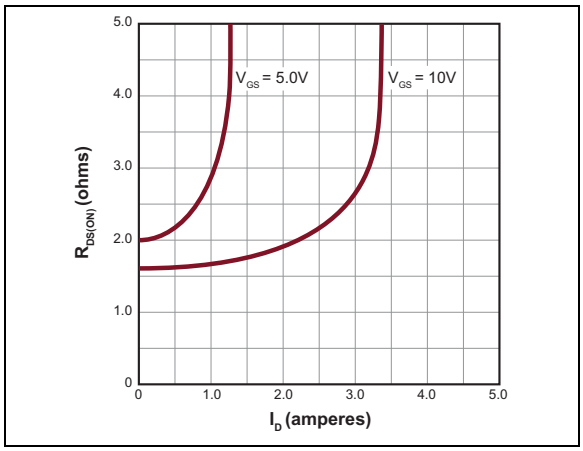


FIGURE 2-10: *On-Resistance vs. Drain Current.*

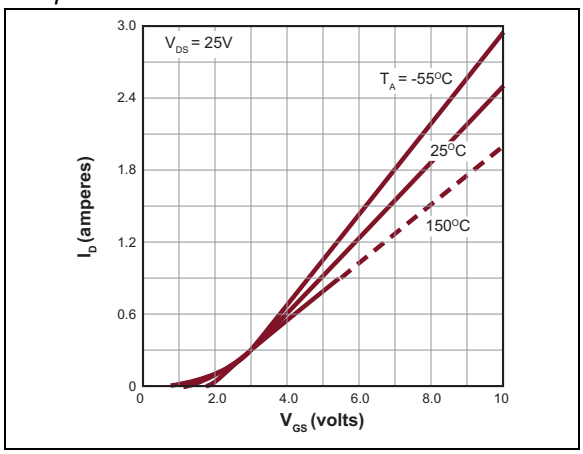


FIGURE 2-8: *Transfer Characteristics.*

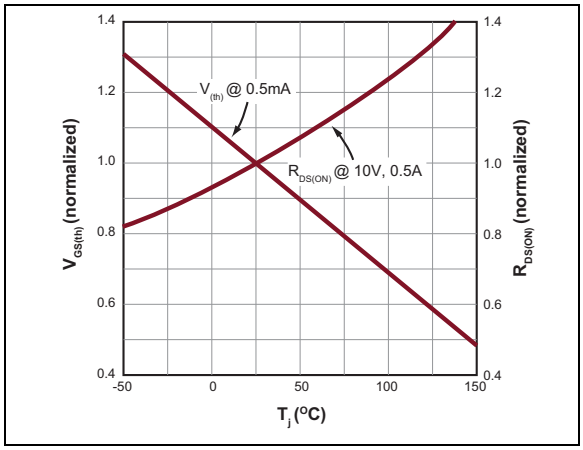


FIGURE 2-11: *$V_{GS(th)}$ and R_{DS} Variation with Temperature.*

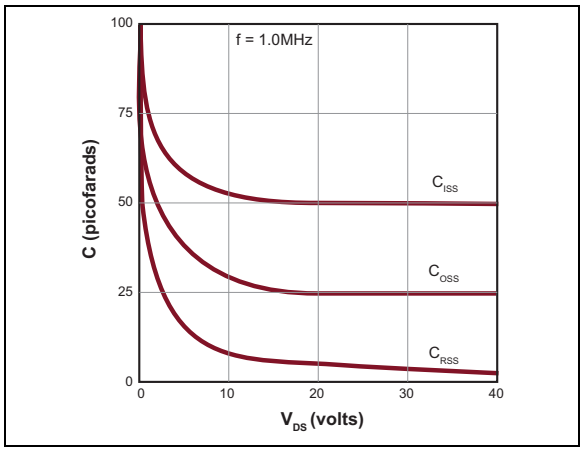


FIGURE 2-9: *Capacitance vs. Drain-to-Source Voltage.*

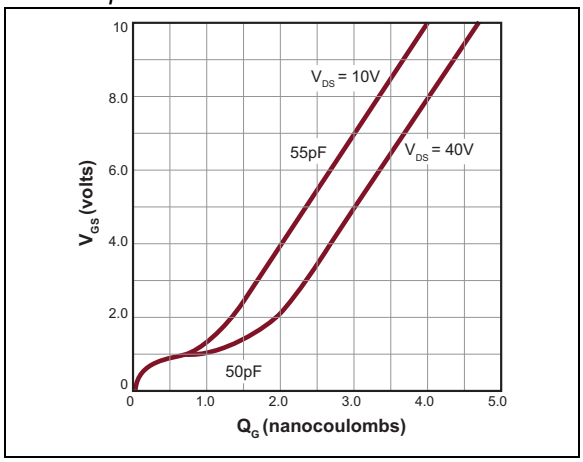


FIGURE 2-12: *Gate Drive Dynamic Characteristics.*

3.0 PIN DESCRIPTION

Table 3-1 shows the description of pins in TN0110.
Refer to **Package Type** for the location of pins.

TABLE 3-1: PIN FUNCTION TABLE

Pin Number	Pin Name	Description
1	Source	Source
2	Gate	Gate
3	Drain	Drain

4.0 FUNCTIONAL DESCRIPTION

Figure 4-1 illustrates the switching waveforms and test circuit for TN0110.

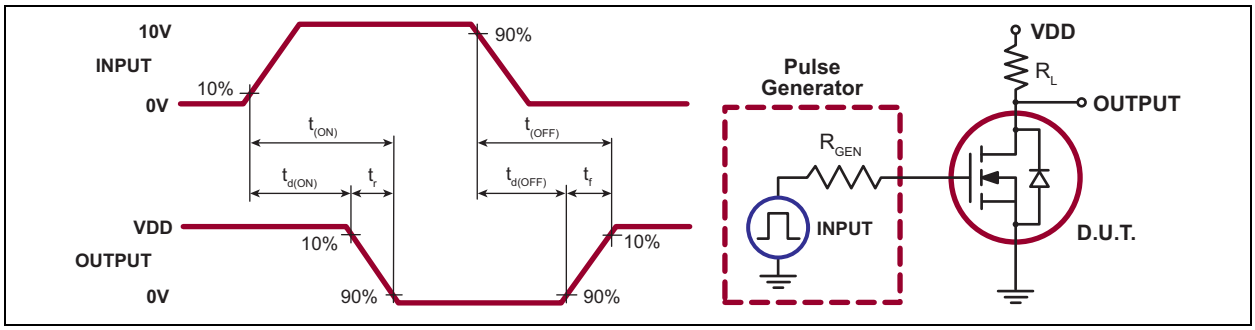


FIGURE 4-1: *Switching Waveforms and Test Circuit.*

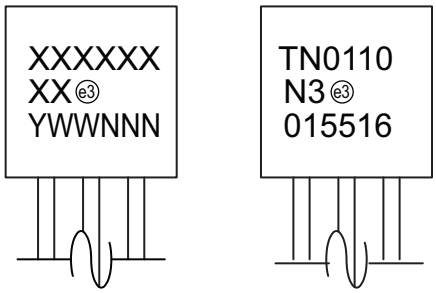
TABLE 4-1: PRODUCT SUMMARY

BV_{DSS}/BV_{DGS} (V)	$R_{DS(ON)}$ (Maximum) (Ω)	$I_{D(ON)}$ (Minimum) (A)	$V_{GS(th)}$ (Maximum) (V)
100	3	2	2

5.0 PACKAGING INFORMATION

5.1 Package Marking Information

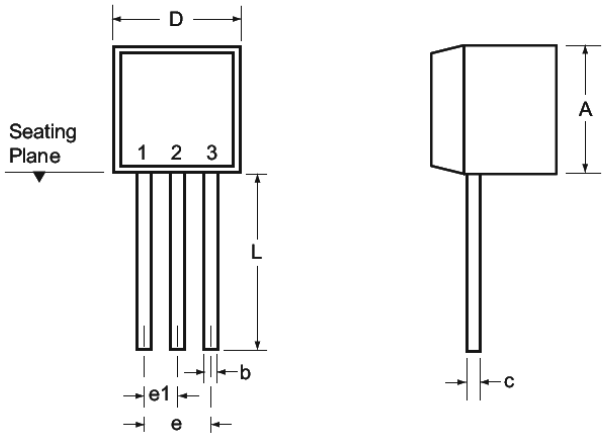
3-lead TO-92 Example

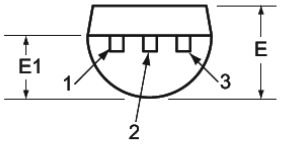


Legend:	XX...X	Product Code or Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week ‘01’)
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC® designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. Package may or not include the corporate logo.

3-Lead TO-92 Package Outline (L/LL/N3)





Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Symbol		A	b	c	D	E	E1	e	e1	L
Dimensions (inches)	MIN	.170	.014†	.014†	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022†	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.
** This dimension is not specified in the JEDEC drawing.*
† This dimension differs from the JEDEC drawing.
Drawings not to scale.

NOTES:

APPENDIX A: REVISION HISTORY

Revision A (September 2020)

- Converted Supertex Docs# DSFP-TN0110 to Microchip DS20006417A
- Changed the package marking format
- Updated the packing medium of the TN0110 N3 P002 media type from 2000/Reel to 2000/Reel (Reverse T/R) to align it with the actual BQM
- Made minor text changes throughout the document

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

PART NO.	XX	-	X	-	X
Device	Package Options		Environmental		Media Type

Device:	TN0110	=	N-Channel Enhancement-Mode Vertical DMOS FET
Package:	N3	=	3-lead TO-92
Environmental:	G	=	Lead (Pb)-free/RoHS-compliant Package
Media Types:	(blank)	=	1000/Bag for an N3 Package
	P003	=	2000/Reel for an N3 Package
	P002	=	2000/Reel (Reverse T/R) for an N3 Package

Examples:

a) TN0110N3-G:	N-Channel Enhancement-Mode, Vertical DMOS FET, 3-lead TO-92,1000/Bag
b) TN0110N3-G-P003:	N-Channel Enhancement-Mode, Vertical DMOS FET, 3-lead TO-92, 2000/Reel
c) TN0110N3-G-P002:	N-Channel Enhancement-Mode, Vertical DMOS FET, 3-lead TO-92, 2000/Reel (Reverse T/R)

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